

CORRECTION

View Article Online
View Journal | View Issue



Cite this: *Energy Environ. Sci.*,
2020, 13, 1287

DOI: 10.1039/d0ee90012e

rsc.li/ees

Correction: Ultrahigh power factor and flexible silver selenide-based composite film for thermoelectric devices

Yao Lu,^a Yang Qiu,^b Kefeng Cai,^{*a} Yufei Ding,^a Mengdi Wang,^c Cong Jiang,^a
Qin Yao,^c Changjun Huang,^a Lidong Chen^{*cd} and Jiaqing He^{*b}

Correction for 'Ultrahigh power factor and flexible silver selenide-based composite film for thermoelectric devices' by Yao Lu et al., *Energy Environ. Sci.*, 2020, DOI: 10.1039/c9ee01609k.

Following publication of this article the authors noted that the thickness of the films, which affects the electrical conductivity, is affected by the synthesis temperature of the silver selenide-based nanowires. When the experiments were repeated the room temperature was around 10 °C higher than when the original experiments were performed and this may influence the quality of the synthesized nanowires and finally the properties of the films.

The experiments have been redone in order to obtain repeatable data which differs slightly to that published in the original article. The authors wish to replace Fig. 2, 4 and S4 with new figures as follows. This correction does not affect any other data or change any of the scientific conclusions in the article.

Fig. 2 should be replaced by:

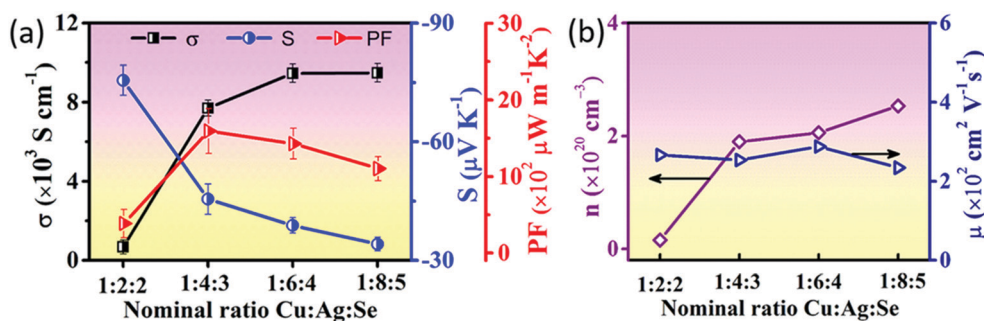


Fig. 2 Room temperature TE parameters (a), carrier concentration and mobility (b) of the $\text{Cu}_x\text{Ag}_{1-x}\text{Se}_y$ films starting from different Cu/Ag/Se nominal molar ratios.

^a Key Laboratory of Advanced Civil Engineering Materials, Ministry of Education, School of Materials Science & Engineering, Tongji University, 4800 Caoan Road, Shanghai 201804, China. E-mail: kfcai@tongji.edu.cn

^b Materials Characterization and Preparation Center and Department of Physics, Southern University of Science and Technology, Shenzhen 518055, China. E-mail: hejq@sustc.edu.cn

^c State Key Laboratory of High Performance Ceramics and Superfine Microstructure, Shanghai Institute of Ceramics, Chinese Academy of Science, Shanghai, 200050, China. E-mail: cld@mail.sic.ac.cn

^d Center of Materials Science and Optoelectronics Engineering, University of Chinese Academy of Sciences, Beijing 100049, China



Fig. 4 should be replaced by:

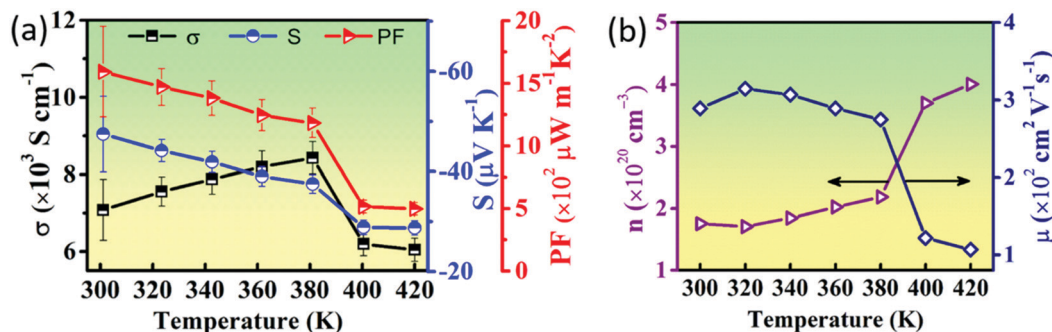


Fig. 4 Temperature dependence of the TE parameters (a), carrier concentration and mobility (b) for the Cu₁Ag₄Se₃ film.

Supplementary Fig. S4 should be replaced by:

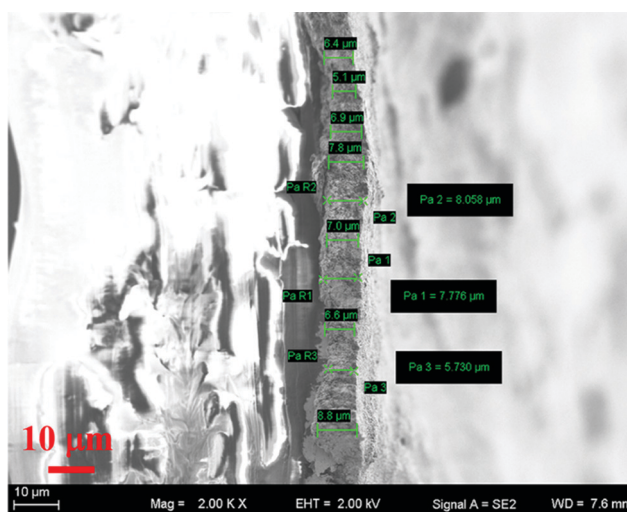


Fig. S4 A typical fractured surface SEM image of the composite films.

The authors also wish to replace the data related to Fig. 2, 4 and S4 in the manuscript. For example, “2231.5 $\mu\text{W m}^{-1} \text{ K}^{-2}$,” should read as “1593.9 $\mu\text{W m}^{-1} \text{ K}^{-2}$,” and “ $zT \sim 0.5$ at 300 K” should read as “ $zT \sim 0.4$ at 300 K”.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

